Supplementary Materials: In Situ Synthesis of High Thermoelectric Performance Bi2Te3 Flexible Thin Films Through Thermal Diffusion Engineering

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**Figure S1.** The thermoelectric performance of Bi2Te3 prepared at 668 K.

**Table S1.** The atomic percent of Bi2Te3 prepared at 668 K.

|  |  |  |  |
| --- | --- | --- | --- |
| **Temperature (K)** | **Bi (at%)** | **Te (at%)** | **Bi∶Te** |
| 668 | 43.1 | 56.9 | 2:2.64 |